Title: ASYMMETRIC BAND-GAP ENGINEERED NONVOLATILE MEMORY DEVICE

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## IN THE DRAWINGS

The drawings were objected to because the labels FLOATING GATE in Fig. 1; GND and 12V in Figs. 3-4; SOURCE ELECTRODE (SE) in Fig. 14 Prior Art were not associated with an arrow. Fig. 1 has been amended to remove the text FLOATING GATE. Figs. 3-4 has been amended to include a lead line with the text GND and 12V. With respect to SOURCE ELECTRODE (SE), Applicant notes that the specification states: The illustrated device is fabricated on a silicon substrate 1412 such as a p silicon substrate or p-well in which case it is referred to as a source electrode (SE), and is separated from other devices by the isolation trenches 1414. Specification at page 24 lines 9-12. Thus, the substrate 1412 can form a source electrode. SOURCE ELECTRODE (SE) is written in the area of the substrate 1414 in a similar manner as PROGRAM ELECTRODE (PE) is written in the area of the control gate 1430. Applicant believes that this is permissible, and is useful to describe the subject matter. Should the Examiner disagree, Applicant respectfully requests the Examiner to contact the Applicant's representative to address this issue.

The drawings were objected to as failing to comply with 37 CFR 1.84(p)(5) because they include the following not mentioned in the description: 216, 220, 1.1ev, 9ev, 5.0ev and in Fig. 2; 1.1ev, 9ev, 5.0ev, and 5.7ev in Figs. 3-4; 10 M SEC Fig. 5; n and ARROW INDICATES EXPERIMENTAL RATIOS in Fig. 9 Prior Art. The specification has been amended to include a first insulator region 216 and a second insulator region 220. The first and second insulator regions 216 and 220 generally correspond to the first and second insulator regions 116 and 120, respectively, in Figure 1. Applicant asserts that no new matter has been added. Applicant respectfully asserts that 1.1 ev, 9 ev, 5.0 ev in Fig. 2 and 2.2 ev, 9 ev, 5.0 ev and 5.7 ev in Figs. 3-4 are not reference characters per 37 CFR §1.84(p)(5), but rather are graphical drawing symbols per 37 CFR §1.84(n) having a conventional meaning for band-gap diagrams. These graphical symbols clarify the values of the energy barriers identified in the specification. Fig. 5 has been amended to remove 10 M SEC, and Fig. 9 has been amended to remove n and ARROW INDICATES EXPERIMENTAL RATIOS.

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The drawings were objected to as failing to comply with 37 CFR 1.84(p)(5) because they do not include reference signs mentioned in the description. The objection identified the following: 2.5 E6 V/CM (line 25, page 16; line 11, page 17); 4E6 V/CM (line 8, page 17) (Vsx) (lines 1, 12, and 22, page 18); 1 to 10 msec (line 5, page 18); 7E6 V/CM (lines 23-24, page 20); 12E6 V/CM (line 24, page 20); PE (line 11, page 25); SE (line 12, page 25); 1424 (line 16, page 24). Applicant respectfully asserts that 2.5 E6 V/CM, 4E6 V/CM, 1 to 10 msec, 7E6 V/CM, and 12E6 V/CM are values of a field, are not reference signals, and thus do not fall under 37 CFR §1.84(p)(5). Applicant respectfully asserts that  $V_{SX}$  has a conventional meaning and is included in parentheses after the term substrate voltage for the ease of the reader, and further asserts that  $V_{SX}$  is not a reference signal, and thus does not fall under 37 CFR §1.84(p)(5). Applicant respectfully asserts that PE and SE are not reference signals, and thus do not fall under 37 CFR §1.84(p)(5). The control gate can also be referred to as a programming electrode (PE), and is identified with reference number 1530. The substrate can also be referred to a source electrode (SE), and is identified with reference number 1512. With respect to reference number 1424, Applicant has amended Fig. 14 to replace reference number 1429 with 1424 to reference the bit line contact.

Corrected drawings (Replacement Sheets) for Figures 1, 5, 6, 8, 9, 14, 15, 16, 17, 18, 19 are supplied herewith. The amendment to Fig. 1 removes the text FLOATING GATE. The amendment to Figs. 3-4 adds lead lines for GND and +12V. The amendment to Figs. 5-6 removes the text 10 M SEC. The amendment to Fig. 8 removes the text FLOATING PLATE. The amendment to Fig. 9 removes the text "n," "ARROW INDICATES EXPERIMENTAL RATIOS," and the arrows along the axes of the graph. The amendment to Fig. 14 replaces 1429 with 1424 to identify the bit contact, and replaces SOURCE ELECTODE with SOURCE ELECTRODE. The amendment to Figs. 15-19 removes equations and dimensions. The specification includes this removed text.